

TENTATIVE

- Features
- Monolithic N-channel MOSFET built in.
 - Ultralow on resistance.
 - Charge pump built in.
 - SENCE MOS built in.

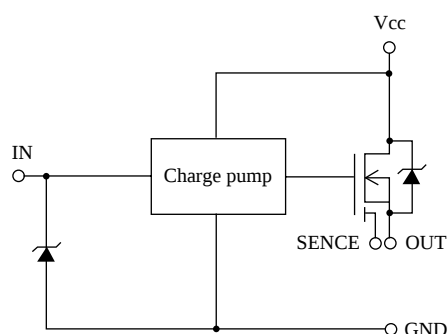
Absolute Maximum Ratings / Ta=25°C

			unit
Supply Voltage	V _{CC}	-0.3 to 30	V
Input Voltage	V _{IN}	-0.3 to 10	V
Output Current	I _{OUT}	8	A
Power Dissipation	P _D (Tc=25°C)	2	W
Operating Temperature	T _{opr}	-40 to 150	°C
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Operating Voltage	V _{CCOP}		5		30	V
Sleep Mode Supply Current	I _{CCOFF}	V _{CC} =15V, V _{IN} =0V		15		μA
Supply Current	I _{CCON}	V _{CC} =15V, V _{IN} =5V		1.5		mA
Input Threshold Voltage	V _{IN(th)}		0.5		1.5	V
Input Current (ON)	I _{ION}	V _{CC} =15V, V _{IN} =10V			1	μA
Input Current (OFF)	I _{IOFF}	V _{CC} =15V, V _{IN} =0.4V			1	μA
On State Resistance	R _{DS(on)}	V _{CC} =15V, I _{OUT} =1A		25	38	mΩ

Block Diagram



Case Outline

SOP8(unit:mm)

